

COMPLEMENTARY SILICON POWER TRANSISTORS

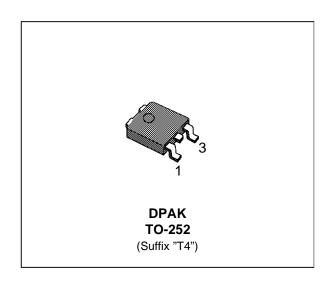
- SGS-THOMSON PREFERRED SALESTYPES
- SURFACE-MOUNTING TO-252 (DPAK)
 POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICAL SIMILAR TO BD909 AND BD910

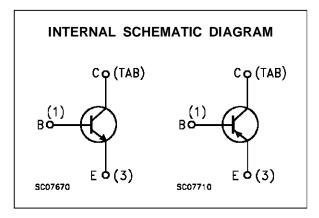
APPLICATIONS

 GENERAL PURPOSE SWITCHING AND AMPLIFIER

DESCRIPTION

The STD909 and the STD910 form complementary NPN-PNP pairs. They are manufactured using Epitaxial Base technology for cost-effective performance.





ABSOLUTE MAXIMUM RATINGS

Symbol Parameter		Value	Unit	
V _{CBO}	Collector-Base Voltage (I _E = 0)	80	V	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	80	V	
V _{EBO} Emitter-Base Voltage (I _C = 0)		5	V	
Ic	Collector Current	15	А	
Ι _Β	Base Current	5	А	
P_{tot}	Total Dissipation at T _c = 25 °C	20	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
T _j Max. Operating Junction Temperature		150	°C	

For PNP type voltage and current values are negative.

January 1995 1/6

THERMAL DATA

ſ	R _{thj-case}	Thermal Resistance	Junction-case	Max	6.25	°C/W
	R _{thj-amb}	Thermal Resistance	Junction-ambient	Max	100	°C/W

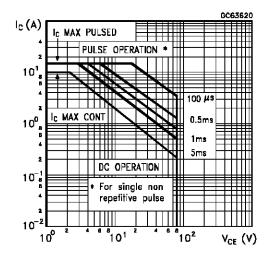
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (i _E = 0)	V _{CB} = 80 V V _{CB} = 80 V T _j = 150 °C			0.01 2	mA mA
I _{CEO}	Collector Cut-off Current (i _B = 0)	V _{CB} = 40 V			0.01	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			0.1	mA
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	80			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A I _B = 0.5 A I _C = 10 A I _B = 2.5 A			1 3	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 10 A I _B = 2.5 A			2.5	V
V _{BE} *	Base-Emitter Voltage	I _C = 5 A V _{CE} = 4 V			1.5	V
h _{FE} *	DC Current Gain	Ic = 0.5 A	40 15 5		250 150	
f⊤	DC Current Gain	Ic = 0.5 A VcE = 4 V	3			MHz

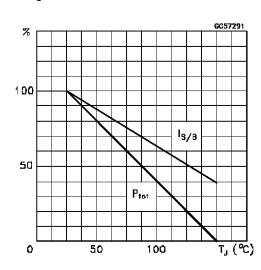
 $[\]ast$ Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

For PNP type voltage and current values are negative.

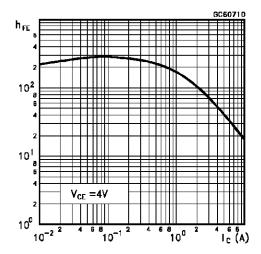
Safe Operating Areas



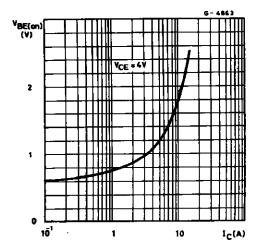
Derating Curve



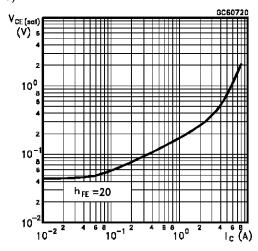
DC Current Gain (NPN type)



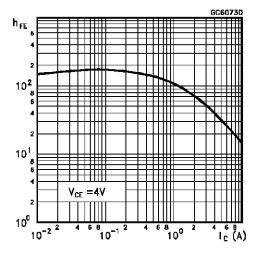
DC Transconductance (NPN type)



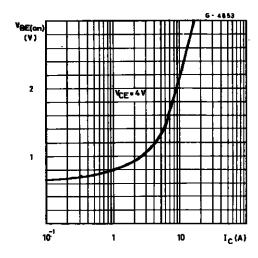
Collector-Emitter Saturation Voltage (NPN type)



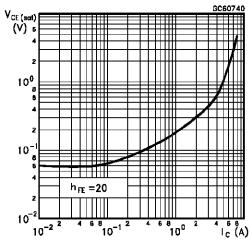
DC Current Gain (PNP type)



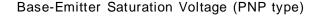
DC Transconductance (PNP type)

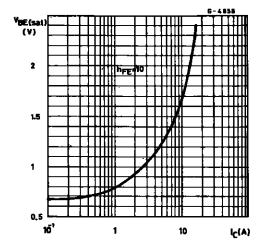


Collector-Emitter Saturation Voltage (PNP type)

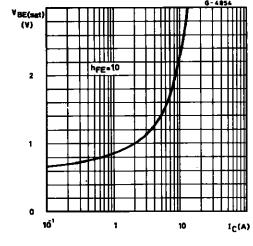


Base-Emitter Saturation Voltage (NPN type)

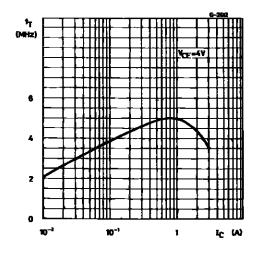


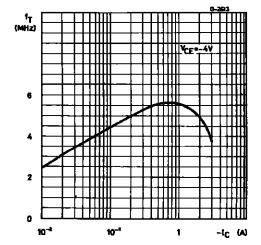


Transition Frequency (NPN types)



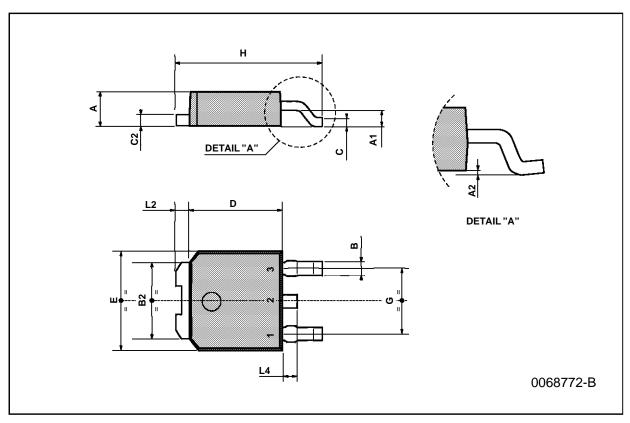
Transition Frequency (PNP types)





TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	2.2		2.4	0.086		0.094	
A1	0.9		1.1	0.035		0.043	
A2	0.03		0.23	0.001		0.009	
В	0.64		0.9	0.025		0.035	
B2	5.2		5.4	0.204		0.212	
С	0.45		0.6	0.017		0.023	
C2	0.48		0.6	0.019		0.023	
D	6		6.2	0.236		0.244	
E	6.4		6.6	0.252		0.260	
G	4.4		4.6	0.173		0.181	
Н	9.35		10.1	0.368		0.397	
L2		0.8			0.031		
L4	0.6		1	0.023		0.039	



STD909 STD910

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